

# FDS4435BZ

## P-Channel PowerTrench® MOSFET -30V, -8.8A, 20mΩ

### Features

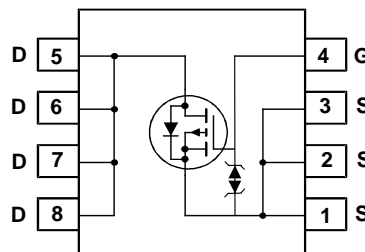
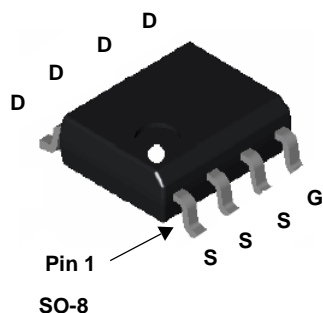
- Max  $r_{DS(on)}$  = 20mΩ at  $V_{GS} = -10V$ ,  $I_D = -8.8A$
- Max  $r_{DS(on)}$  = 35mΩ at  $V_{GS} = -4.5V$ ,  $I_D = -6.7A$
- Extended  $V_{GSS}$  range (-25V) for battery applications
- HBM ESD protection level of ±3.8KV typical (note 3)
- High performance trench technology for extremely low  $r_{DS(on)}$
- High power and current handling capability
- Termination is Lead-free and RoHS compliant



### General Description

This P-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been especially tailored to minimize the on-state resistance.

This device is well suited for Power Management and load switching applications common in Notebook Computers and Portable Battery Packs.



### MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DS}$	Drain to Source Voltage	-30	V
$V_{GS}$	Gate to Source Voltage	±25	V
$I_D$	Drain Current -Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	-8.8	A
	-Pulsed	-50	
$P_D$	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	2.5	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1b)	1.0	
$E_{AS}$	Single Pulse Avalanche Energy (Note 4)	24	mJ
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	25	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDS4435BZ	FDS4435BZ	SO-8	13"	12mm	2500units

**Electrical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Off Characteristics**

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = -250\mu\text{A}$ , $V_{GS} = 0\text{V}$	-30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\mu\text{A}$ , referenced to $25^\circ\text{C}$		-21		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -24\text{V}$ , $V_{GS} = 0\text{V}$			1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 25\text{V}$ , $V_{DS} = 0\text{V}$			$\pm 10$	$\mu\text{A}$

**On Characteristics**

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = -250\mu\text{A}$	-1	-2.1	-3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = -250\mu\text{A}$ , referenced to $25^\circ\text{C}$		6		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = -10\text{V}$ , $I_D = -8.8\text{A}$		16	20	m $\Omega$
		$V_{GS} = -4.5\text{V}$ , $I_D = -6.7\text{A}$		26	35	
		$V_{GS} = -10\text{V}$ , $I_D = -8.8\text{A}$ , $T_J = 125^\circ\text{C}$		22	28	
$g_{FS}$	Forward Transconductance	$V_{DS} = -5\text{V}$ , $I_D = -8.8\text{A}$		24		S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = -15\text{V}$ , $V_{GS} = 0\text{V}$ , $f = 1\text{MHz}$		1385	1845	pF
$C_{oss}$	Output Capacitance			275	365	pF
$C_{rss}$	Reverse Transfer Capacitance			230	345	pF
$R_g$	Gate Resistance	$f = 1\text{MHz}$		4.5		$\Omega$

**Switching Characteristics**

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -15\text{V}$ , $I_D = -8.8\text{A}$ , $V_{GS} = -10\text{V}$ , $R_{GEN} = 6\Omega$		10	20	ns
$t_r$	Rise Time			6	12	ns
$t_{d(off)}$	Turn-Off Delay Time			30	48	ns
$t_f$	Fall Time			12	22	ns
$Q_g$	Total Gate Charge	$V_{GS} = 0\text{V}$ to $-10\text{V}$	$V_{DD} = -15\text{V}$ , $I_D = -8.8\text{A}$	28	40	nC
$Q_g$	Total Gate Charge	$V_{GS} = 0\text{V}$ to $-5\text{V}$		16	23	nC
$Q_{gs}$	Gate to Source Charge			5.2		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			7.4		nC

**Drain-Source Diode Characteristics**

$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}$ , $I_S = -8.8\text{A}$ (Note 2)		-0.9	-1.2	V
$t_{rr}$	Reverse Recovery Time	$I_F = -8.8\text{A}$ , $di/dt = 100\text{A}/\mu\text{s}$		29	44	ns
$Q_{rr}$	Reverse Recovery Charge			23	35	nC

## NOTES:

1.  $R_{\theta JA}$  is determined with the device mounted on a  $1\text{in}^2$  pad 2 oz copper pad on a  $1.5 \times 1.5\text{in.}$  board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a.  $50^\circ\text{C}/\text{W}$  when mounted on a  $1\text{in}^2$  pad of 2 oz copper.



b.  $125^\circ\text{C}/\text{W}$  when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width  $< 300\mu\text{s}$ , Duty cycle  $< 2.0\%$ .

3. The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

4. Starting  $T_J = 25^\circ\text{C}$ ,  $L = 1\text{mH}$ ,  $I_{AS} = -7\text{A}$ ,  $V_{DD} = -30\text{V}$ ,  $V_{GS} = -10\text{V}$

## Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

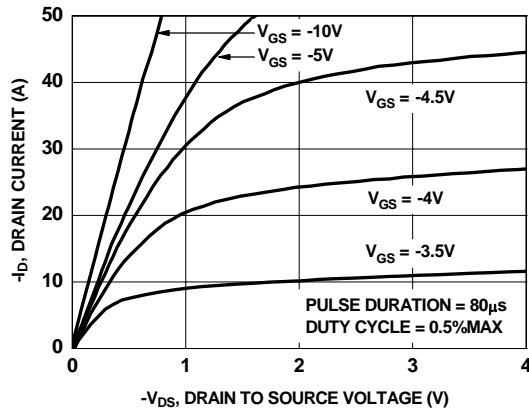


Figure 1. On-Region Characteristics

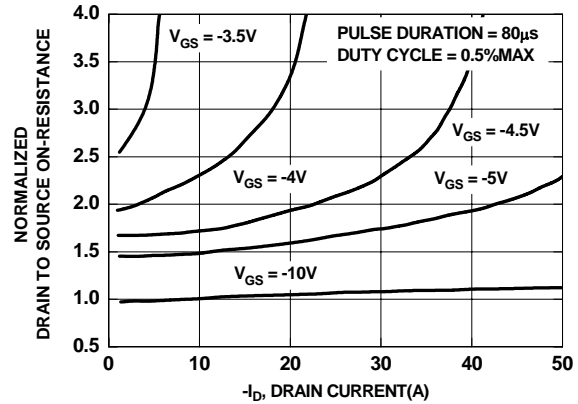


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

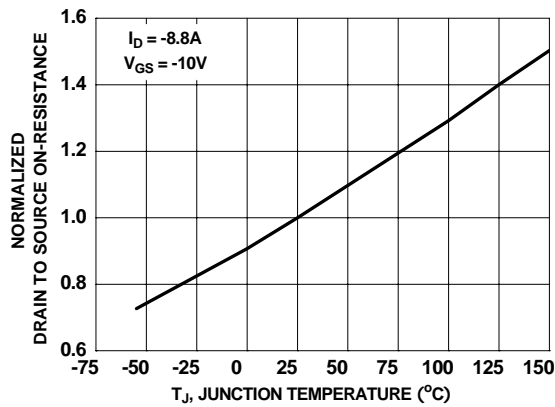


Figure 3. Normalized On-Resistance vs Junction Temperature

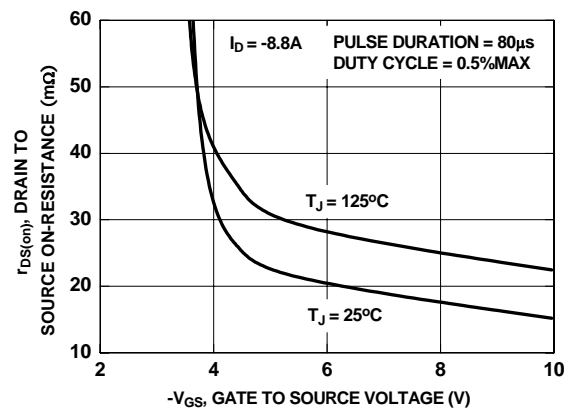


Figure 4. On-Resistance vs Gate to Source Voltage

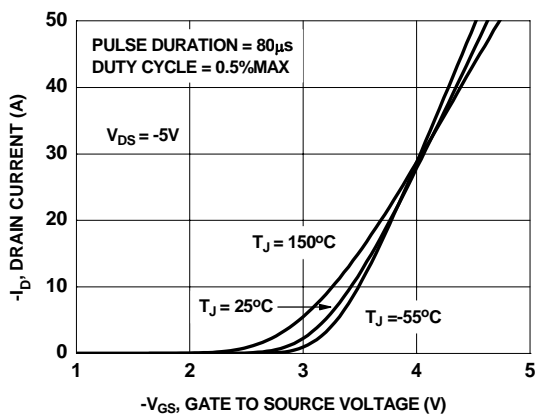


Figure 5. Transfer Characteristics

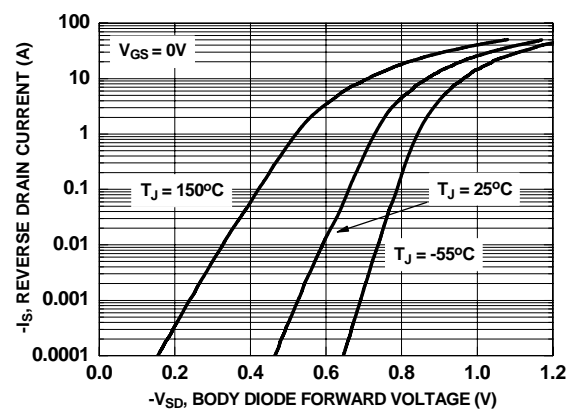


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

## Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

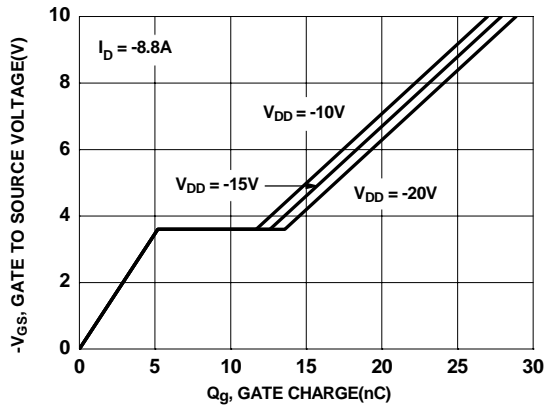


Figure 7. Gate Charge Characteristics

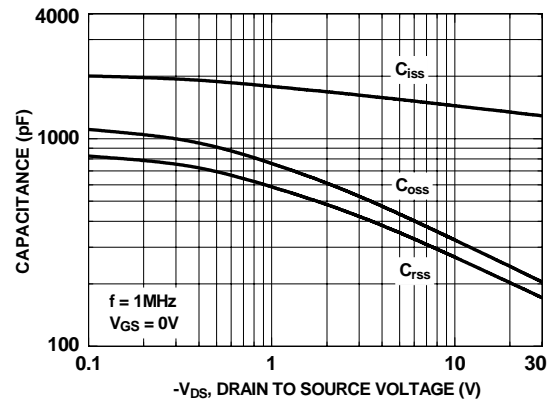


Figure 8. Capacitance vs Drain to Source Voltage

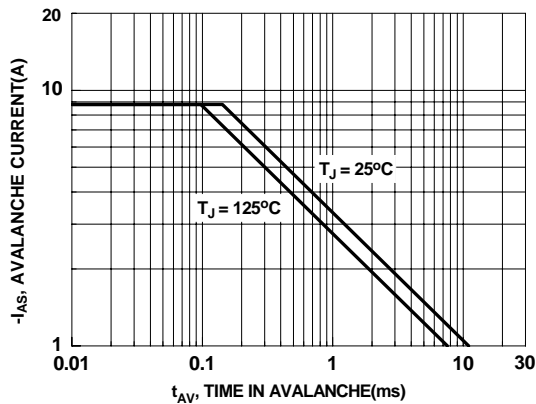


Figure 9. Unclamped Inductive Switching Capability

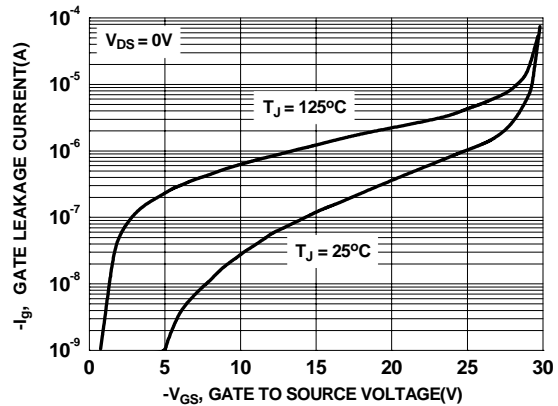


Figure 10. Gate Leakage Current vs Gate to Source Voltage

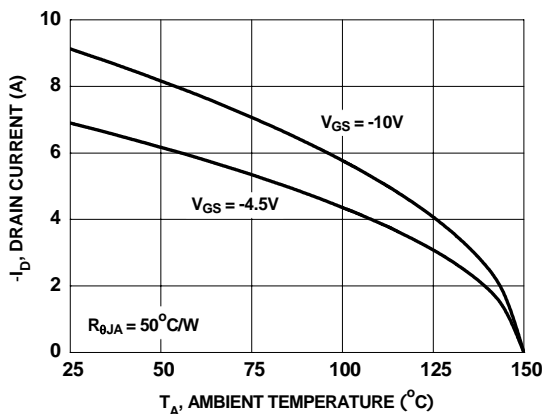


Figure 11. Maximum Continuous Drain Current vs Ambient Temperature

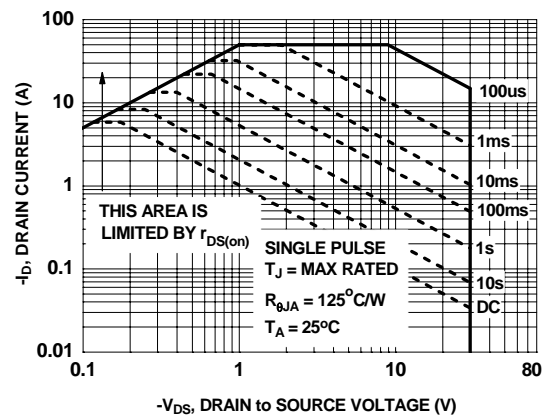


Figure 12. Forward Bias Safe Operating Area

# Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

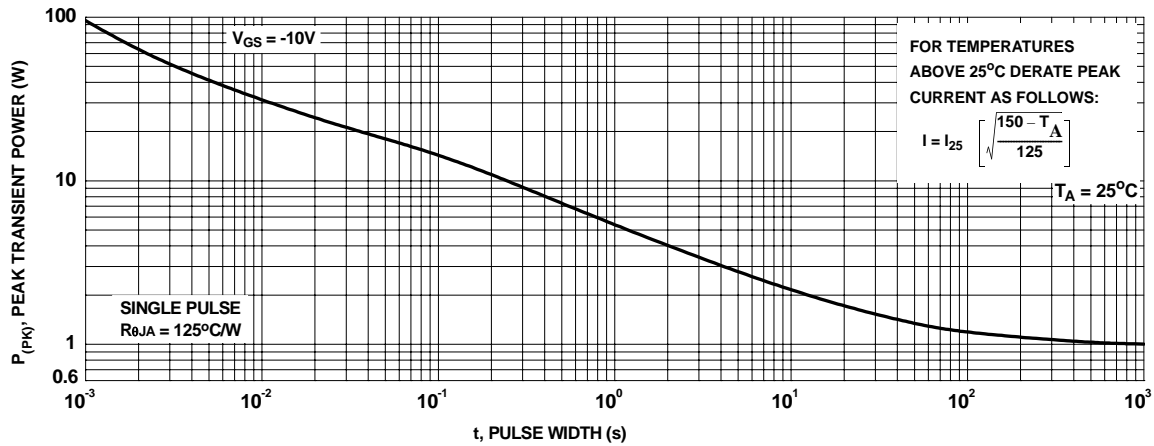


Figure 13. Single Pulse Maximum Power Dissipation

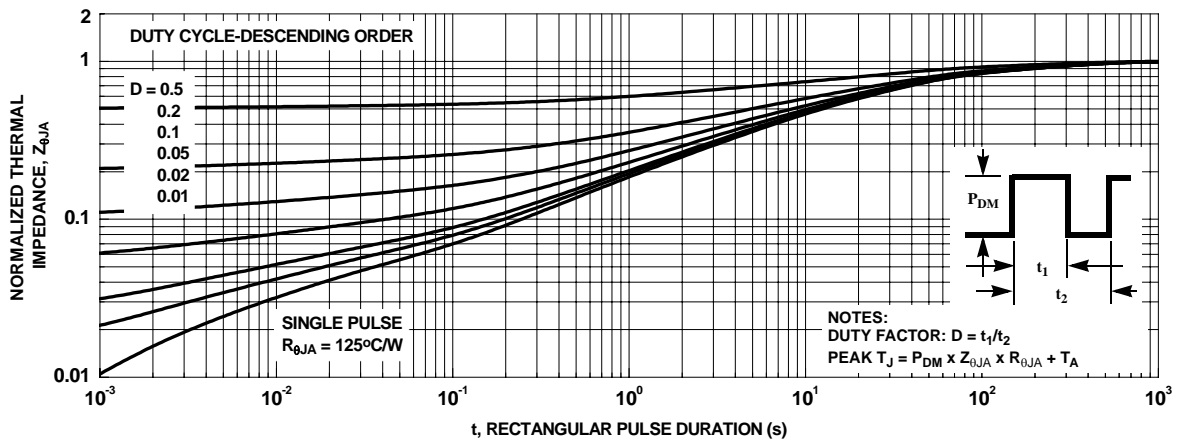


Figure 14. Transient Thermal Response Curve



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